

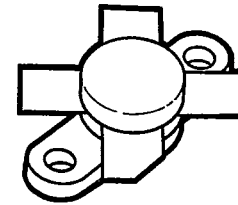


T-33-13

## PT9798

## SSB Power Transistors

- All Gold (Monometallic) Metallization System for Highest Reliability
- Diffused Emitter Ballast Resistors for Ruggedness
- Suitable for Class A, AB and C Operation
- 50 Volt Operation
- 75 Watts
- 15dB Gain
- $\infty$  VSWR



.380 SOE F

## Electrical Characteristics (TFLANGE = 25°C)

	SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	MAX.	UNITS
DC TEST	BVEBO	Emitter to Base Breakdown Voltage	I <sub>B</sub> = 5.0mA	4.0		VDC
	BVCBO	Collector to Base Breakdown Voltage	I <sub>C</sub> = 100mA	110		VDC
	BVCEO	Collector to Emitter Breakdown Voltage	I <sub>C</sub> = 50mA	55		VDC
	hFE	DC Current Gain	V <sub>CE</sub> = 5V I <sub>C</sub> = 1.0A	10	70	
RF TEST	P <sub>OUT</sub>	Power Output	V <sub>CE</sub> = 50V P <sub>IN</sub> = 2.35W f <sub>1</sub> = 28 MHz	75		Watts
	IMD	Intermodulation Distortion	V <sub>CE</sub> = 50V P <sub>OUT</sub> = 75W f <sub>1</sub> = 28 MHz		-32	dB
	VSWR	Mismatch Tolerance	V <sub>CE</sub> = 50V P <sub>OUT</sub> = 75W PEP f <sub>1</sub> = 28 MHz	$\infty$ :1		VSWR
MAX. RATINGS	$\theta_{JF}$	Thermal Resistance Junction to Flange			1.0	°C/W
	I <sub>C(MAX)</sub>	Collector Current	T <sub>F</sub> = 25°C		15	A
	P <sub>T</sub>	Total Dissipation	T <sub>F</sub> = 25°C		150	Watts
	T <sub>STG</sub>	Storage Temperature		-65	150	°C
	T <sub>J(MAX)</sub>	Junction Temperature			200	°C

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Vcc = 50V  
Ico = 60mA  
Pout = 75 Watts

